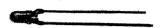


Silicon NPN Epitaxial Planar Phototransistor



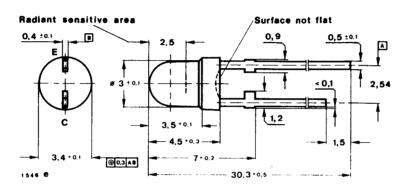
Application: Detector in electronic control and drive circuits

Features:

- Plastic case Ø 3 mm
- Suitable for visible and near infrared radiation
- High sensitivity
- Wide angle of half sensitivity
- Axial terminals

Preliminary specifications

Dimensions in mm



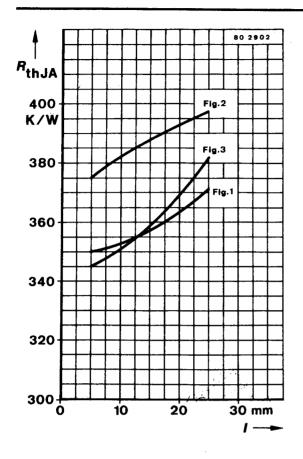
Angle of half sensitivity $\alpha = 180^{\circ}$

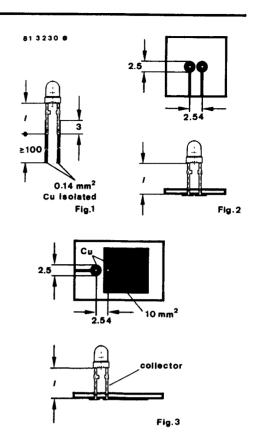
Special case Clear plastic Weight max. 0.35 g

Absolute maximum ratings

Collector-emitter voltage	$V_{\sf CEO}$	32	V
Emitter-collector voltage	V _{ECO}	5	V
Collector current	I _C	50	mA
Peak collector current			
$\frac{t_{\rm p}}{7}$ = 0.5, $t_{\rm p} \le$ 10 ms	I _{CM}	100	mA
Total power dissipation			
$T_{amb} \leq 55^{\circ}C$	P_{tot}	100	mW
Junction temperature	$T_{\mathbf{j}}$	100	°C
Storage temperature range	\mathcal{T}_{stg}	−25 +100	°C
Soldering temperature, maximal			
<i>t</i> ≤ 3 s	$T_{\rm sd}^{-1}$)	245	°C

 $^{^{1})}$ Distance from the touching border \geq 1.5 mm with intermediate PC-board S 1.2.127/0781 E





Thermal resistance		Min.	Тур.	Max.	
Junction ambient	R_{thJA}			450	K/W
Optical and electrical characteristics $T_{amb} = 25 ^{\circ} \text{C}$					
Collector dark current $V_{CE} = 20 \text{ V}, E = 0$	I _{CEO} *)		10	200	nA
Collector light current $V_{\text{CE}} = 5 \text{ V}, E_{\text{A}} = 1 \text{ klx}^{1}$) $V_{\text{CE}} = 5 \text{ V}, E_{\text{e}} = 1 \text{ mW/cm}^{2}, \lambda_{\text{p}} = 950 \text{ nm}$	/ _{ca} l _{ca} *)	0.5	3 1.0		mA mA
Peak wavelength sensitivity	λ_{p}		830		nm
Range of spectral bandwidth (50 %)	λ _{0.5}	560980			nm
Collector-emitter breakdown voltage $I_C = 1 \text{ mA}$	V _{(BR) CEO} *)	32			V
Collector-emitter saturation voltage $I_C = 0.1 \text{mA}$, $E_e = 1 \text{mW/cm}^2$, $\lambda_p = 950 \text{nm}$	V _{CEsat} *)			0.3	V

^{*)} AQL = 0.65 %

¹⁾ Standard illuminant A (DIN 5033/IEC 306-1)

